

SEMITOP[®]4

IGBT module

SK100GH128T

Target Data

Features

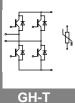
- One screw mounting module
- Fully compatible with SEMITOP[®]1,2,3
- Improved thermal performances
 by aluminium oxide substrate
- SPT IGBT Technology
- CAL technology FWD
- Integrated NTC Temperature sensor

Typical Applications*

Voltage regulator

Absolute Maximum Ratings $T_c = 25 \text{ °C}$, unless otherwise specified					
Symbol	-		Values	Units	
IGBT					
V _{CES}	T _j = 25 °C		1200	V	
I _C	T _j = 125 °C	T _s = 25 °C	120	А	
		T _s = 70 °C	80	А	
I _{CRM}	$I_{CRM}\text{=} 2 \text{ x } I_{Cnom} \text{ , } t_p \leq 1 \text{ms}$		200	А	
V _{GES}			20	V	
t _{psc}	V_{CC} = 600 V; $V_{GE} \le 20$ V; VCES < 1200 V	T _j = 125 °C	10	μs	
Inverse	Diode				
I _F	T _j = 150 °C	T _s = 25 °C	67	А	
		T _s = 70 °C	50	А	
I _{FRM}	I_{FRM} = 2 x I_{Fnom} , $t_p \le 1ms$		110	А	
I _{FSM}	t _p = 10 ms; half sine wave	T _j = 150 °C	550	Α	
Module					
I _{t(RMS)}				А	
Τ _{vj}			-40 +150	°C	
T _{stg}			-40 +125	°C	
V _{isol}	AC, 1 min.		2500	V	

Characteristics T _c =		25 °C, unless otherwise specified				
Symbol	Conditions		min.	typ.	max.	Units
IGBT						
V _{GE(th)}	$V_{GE} = V_{CE}, I_C = 4 \text{ mA}$		4,5	5,5	6,5	V
I _{CES}	V_{GE} = 0 V, V_{CE} = V_{CES}	T _j = 25 °C			0,2	mA
		T _j = 125 °C		0,4		mA
I _{GES}	V_{CE} = 0 V, V_{GE} = 20 V	T _j = 125 °C			400	nA
V _{CE0}		T _j = 25 °C		1,1	1,3	V
		T _j = 125 °C		1	1,2	V
r _{CE}	V _{GE} = 15 V	T _j = 25°C		6		mΩ
		T _j = 125°C		11		mΩ
V _{CE(sat)}	I _{Cnom} = 100 A, V _{GE} = 15 V			1,9	2,3	V
		T _j = 125°C _{chiplev.}		2,1		V
C _{ies}				9		nF
C _{oes}	V_{CE} = 25, V_{GE} = 0 V	f = 1 MHz		0,66		nF
C _{res}				0,42		nF
R _{Gint}	T _j = 25 °C			5		Ω
t _{d(on)}				80		ns
t,	$R_{Gon} = 4 \Omega$	V _{CC} = 600V		33		ns
E _{on}		I _C = 100A		5,97		mJ
t _{d(off)} t	$R_{Goff} = 4 \Omega$ di/dt = 3000 A/µs	T _j = 125 °C		418 70		ns ns
t _f E _{off}	unut - 3000 Arps			8,5		mJ
R _{th(j-s)}	per IGBT	I		0,34		K/W





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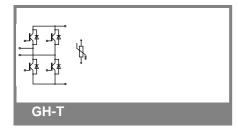
Typical Applications*

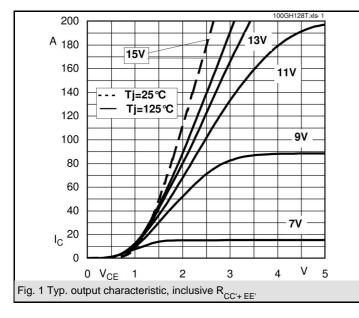
Voltage regulator

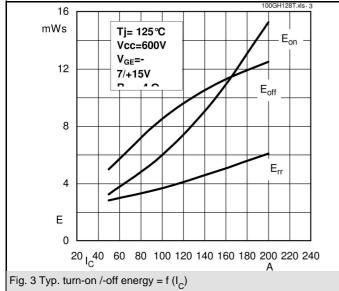
Characte	ristics					
Symbol	Conditions		min.	typ.	max.	Units
Inverse D						
$V_F = V_{EC}$	I_{Fnom} = 55 A; V_{GE} = 0 V	T _j = 25 °C _{chiplev.}		2	2,5	V
		T_j = 125 °C _{chiplev} .		1,8	2,3	V
V _{F0}		T _j = 125 °C		1,2		V
r _F		T _j = 125 °C		10,9		mΩ
I _{RRM}	I _F = 100 A	T _j = 125 °C		125		А
Q _{rr}	di/dt = 3000 A/µs			25		μC
E _{rr}	V _{CC} =600V			3,66		mJ
R _{th(j-s)D}	per diode			0,7	0,85	K/W
Freewhee	eling Diode					
$V_F = V_{EC}$	I_{Fnom} = A; V_{GE} = V	$T_j = °C_{chiplev.}$				V
V _{F0}		T _j = °C				V
r _F		$T_j = °C$ $T_j = °C$				V
I _{RRM}	I _F = A	T _j = °C				А
Q _{rr}						μC
Err						mJ
	per diode					K/W
M _s	to heat sink		2,5		2,75	Nm
w				60		g
Tempera	ture sensor					
R ₁₀₀	T _s = 100°C (R ₂₅ =5kΩ)			493±5%		Ω

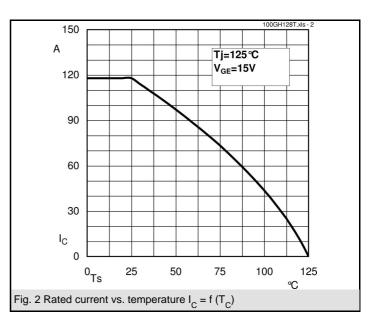
This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

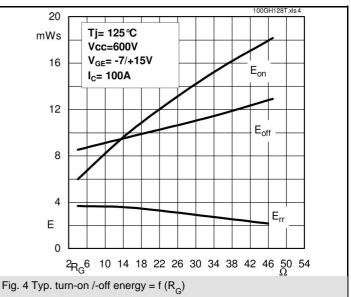
* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

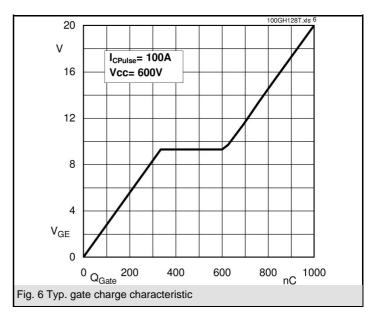


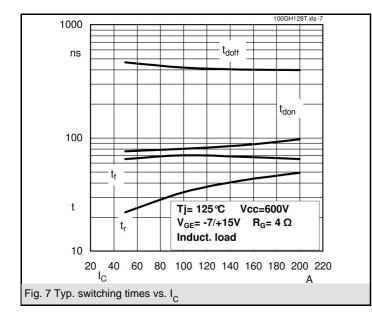


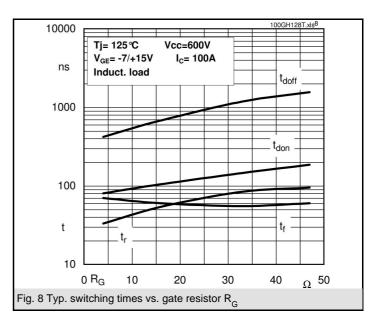


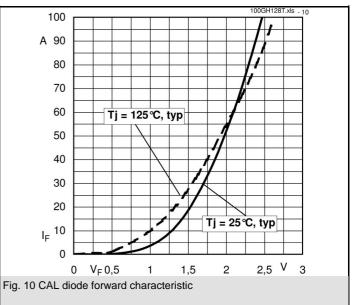




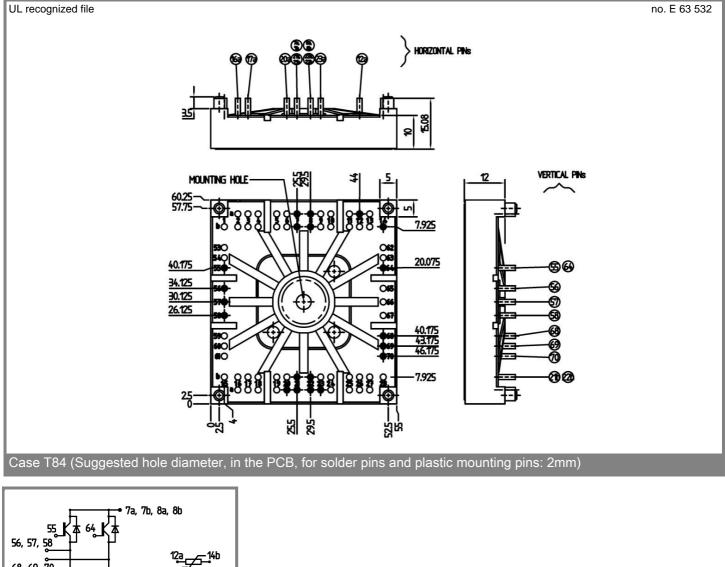








no. E 63 532



68, 69, 70

Case T 84

20a K k 23a k

21a, 21b, 22a, 22b